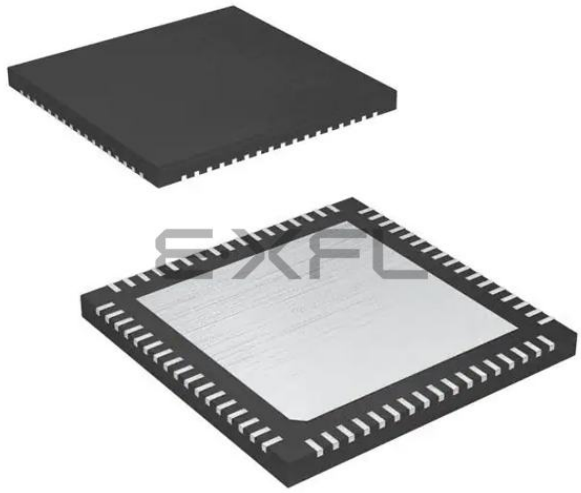

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	8051
Core Size	8-Bit
Speed	50MHz
Connectivity	EBI/EMI, I²C, LINbus, SPI, UART/USART
Peripherals	CapSense, DMA, LCD, POR, PWM, WDT
Number of I/O	38
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 16x12b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	68-VFQFN Exposed Pad
Supplier Device Package	68-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c3445lti-079

Figure 2-6. 100-pin TQFP Part Pinout

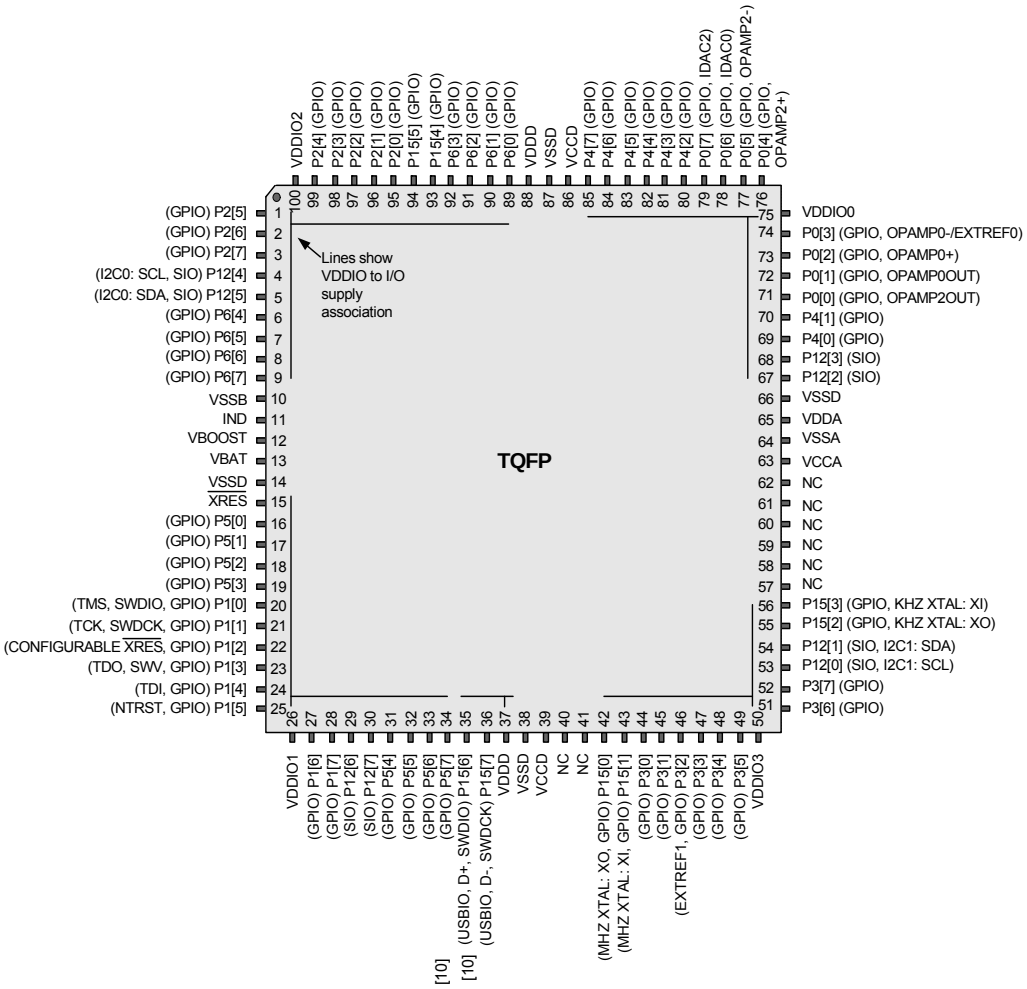


Table 2-1. VDDIO and Port Pin Associations

VDDIO	Port Pins
VDDIO0	P0[7:0], P4[7:0], P12[3:2]
VDDIO1	P1[7:0], P5[7:0], P12[7:6]
VDDIO2	P2[7:0], P6[7:0], P12[5:4], P15[5:4]
VDDIO3	P3[7:0], P12[1:0], P15[3:0]
VDDD	P15[7:6] (USB D+, D-)

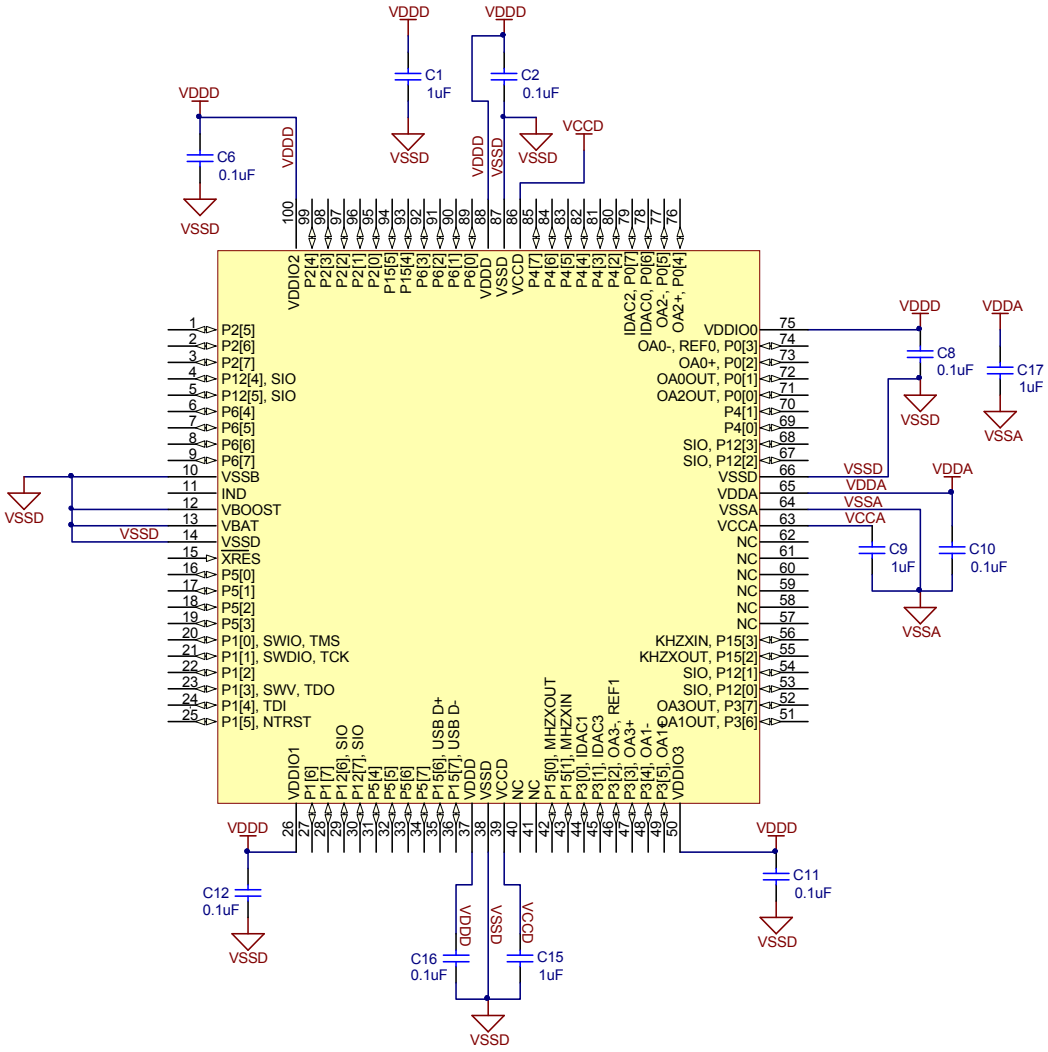
Note
10. Pins are Do Not Use (DNU) on devices without USB. The pin must be left floating.

Figure 2-7 and Figure 2-8 on page 11 show an example schematic and an example PCB layout, for the 100-pin TQFP part, for optimal analog performance on a two-layer board.

- The two pins labeled VDDD must be connected together.
- The two pins labeled VCCD must be connected together, with capacitance added, as shown in Figure 2-7 and Power System on page 30. The trace between the two VCCD pins should be as short as possible.
- The two pins labeled VSSD must be connected together.

For information on circuit board layout issues for mixed signals, refer to the application note AN57821 - Mixed Signal Circuit Board Layout Considerations for PSoC® 3 and PSoC 5.

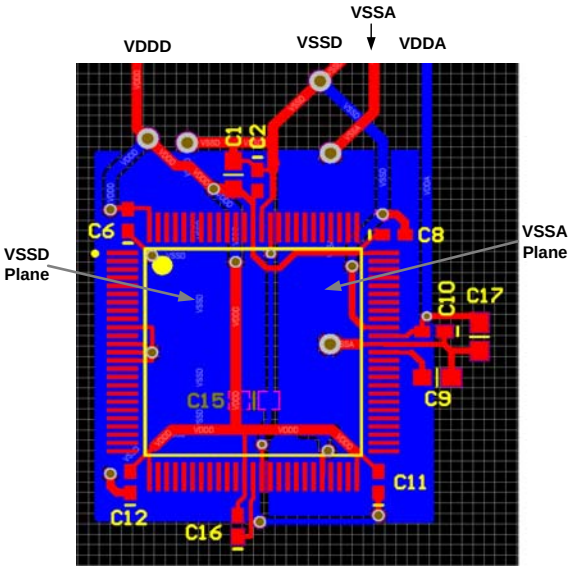
Figure 2-7. Example Schematic for 100-pin TQFP Part With Power Connections



Note The two VCCD pins must be connected together with as short a trace as possible. A trace under the device is recommended, as shown in Figure 2-8 on page 11.

For more information on pad layout, refer to http://www.cypress.com/cad-resources/psoc-3-cad-libraries.

Figure 2-8. Example PCB Layout for 100-pin TQFP Part for Optimal Analog Performance



3. Pin Descriptions

IDAC0, IDAC2

Low resistance output pin for high current DACs (IDAC).

OpAmp0out, OpAmp2out

High current output of uncommitted opamp[11].

Extref0, Extref1

External reference input to the analog system.

Opamp0–, Opamp2–

Inverting input to uncommitted opamp.

Opamp0+, Opamp2+

Noninverting input to uncommitted opamp.

GPIO

General purpose I/O pin provides interfaces to the CPU, digital peripherals, analog peripherals, interrupts, LCD segment drive, and CapSense[11].

I2C0: SCL, I2C1: SCL

I^2C SCL line providing wake from sleep on an address match. Any I/O pin can be used for I^2C SCL if wake from sleep is not required.

I2C0: SDA, I2C1: SDA

I^2C SDA line providing wake from sleep on an address match. Any I/O pin can be used for I^2C SDA if wake from sleep is not required.

Ind

Inductor connection to boost pump.

kHz XTAL: Xo, kHz XTAL: Xi

32.768-kHz crystal oscillator pin.

MHz XTAL: Xo, MHz XTAL: Xi

4- to 25-MHz crystal oscillator pin.

nTRST

Optional JTAG test reset programming and debug port connection to reset the JTAG connection.

SIO

Special I/O provides interfaces to the CPU, digital peripherals and interrupts with a programmable high threshold voltage, analog comparator, high sink current, and high impedance state when the device is unpowered.

SWDCK

Serial wire debug clock programming and debug port connection.

SWDIO

Serial wire debug input and output programming and debug port connection.

SWV

Single wire viewer debug output.

TCK

JTAG test clock programming and debug port connection.

TDI

JTAG test data In programming and debug port connection.

TDO

JTAG test data out programming and debug port connection.

TMS

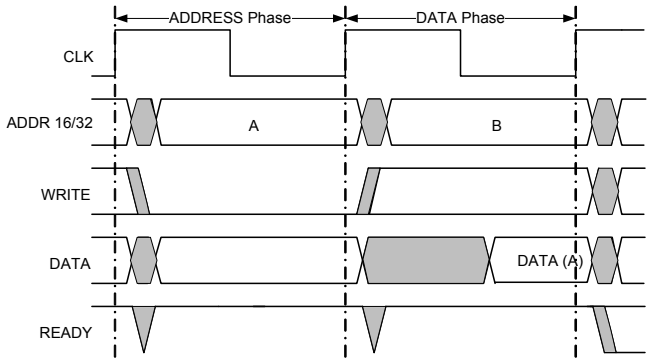
JTAG test mode select programming and debug port connection.

Note
11. GPIOs with opamp outputs are not recommended for use with CapSense.

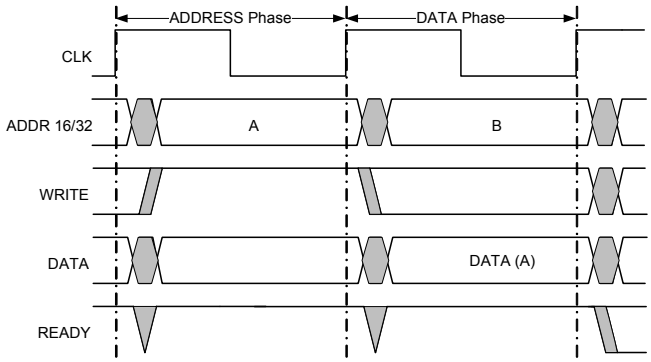
4.4.4.1 Simple DMA

In a simple DMA case, a single TD transfers data between a source and sink (peripherals or memory location). The basic timing diagrams of DMA read and write cycles are shown in Figure 4-1. For more description on other transfer modes, refer to the Technical Reference Manual.

Figure 4-1. DMA Timing Diagram



Basic DMA Read Transfer without wait states



Basic DMA Write Transfer without wait states

4.4.4.2 Auto Repeat DMA

Auto repeat DMA is typically used when a static pattern is repetitively read from system memory and written to a peripheral. This is done with a single TD that chains to itself.

4.4.4.3 Ping Pong DMA

A ping pong DMA case uses double buffering to allow one buffer to be filled by one client while another client is consuming the data previously received in the other buffer. In its simplest form, this is done by chaining two TDs together so that each TD calls the opposite TD when complete.

4.4.4.4 Circular DMA

Circular DMA is similar to ping pong DMA except it contains more than two buffers. In this case there are multiple TDs; after the last TD is complete it chains back to the first TD.

4.4.4.5 Scatter Gather DMA

In the case of scatter gather DMA, there are multiple noncontiguous sources or destinations that are required to effectively carry out an overall DMA transaction. For example, a packet may need to be transmitted off of the device and the packet elements, including the header, payload, and trailer, exist in various noncontiguous locations in memory. Scatter gather DMA allows the segments to be concatenated together by using multiple TDs in a chain. The chain gathers the data from the multiple locations. A similar concept applies for the reception of data onto the device. Certain parts of the received data may need to be scattered to various locations in memory for software processing convenience. Each TD in the chain specifies the location for each discrete element in the chain.

4.4.4.6 Packet Queuing DMA

Packet queuing DMA is similar to scatter gather DMA but specifically refers to packet protocols. With these protocols, there may be separate configuration, data, and status phases associated with sending or receiving a packet.

For instance, to transmit a packet, a memory mapped configuration register can be written inside a peripheral, specifying the overall length of the ensuing data phase. The CPU can set up this configuration information anywhere in system memory and copy it with a simple TD to the peripheral. After the configuration phase, a data phase TD (or a series of data phase TDs) can begin (potentially using scatter gather). When the data phase TD(s) finish, a status phase TD can be invoked that reads some memory mapped status information from the peripheral and copies it to a location in system memory specified by the CPU for later inspection. Multiple sets of configuration, data, and status phase “subchains” can be strung together to create larger chains that transmit multiple packets in this way. A similar concept exists in the opposite direction to receive the packets.

4.4.4.7 Nested DMA

One TD may modify another TD, as the TD configuration space is memory mapped similar to any other peripheral. For example, a first TD loads a second TD’s configuration and then calls the second TD. The second TD moves data as required by the application. When complete, the second TD calls the first TD, which again updates the second TD’s configuration. This process repeats as often as necessary.

4.5 Interrupt Controller

The interrupt controller provides a mechanism for hardware resources to change program execution to a new address, independent of the current task being executed by the main code. The interrupt controller provides enhanced features not found on original 8051 interrupt controllers:

- Thirty two interrupt vectors
- Jumps directly to ISR anywhere in code space with dynamic vector addresses
- Multiple sources for each vector
- Flexible interrupt to vector matching
- Each interrupt vector is independently enabled or disabled
- Each interrupt can be dynamically assigned one of eight priorities
- Eight level nestable interrupts

6: CPU acknowledges the interrupt request

7: ISR address is read by CPU for branching

8, 9: PEND and POST bits are cleared respectively after receiving the IRA from core

10: IRA bit is cleared after completing the current instruction and starting the instruction execution from ISR location (takes 7 cycles)

11: IRC is set to indicate the completion of ISR, Active int. status is restored with previous status

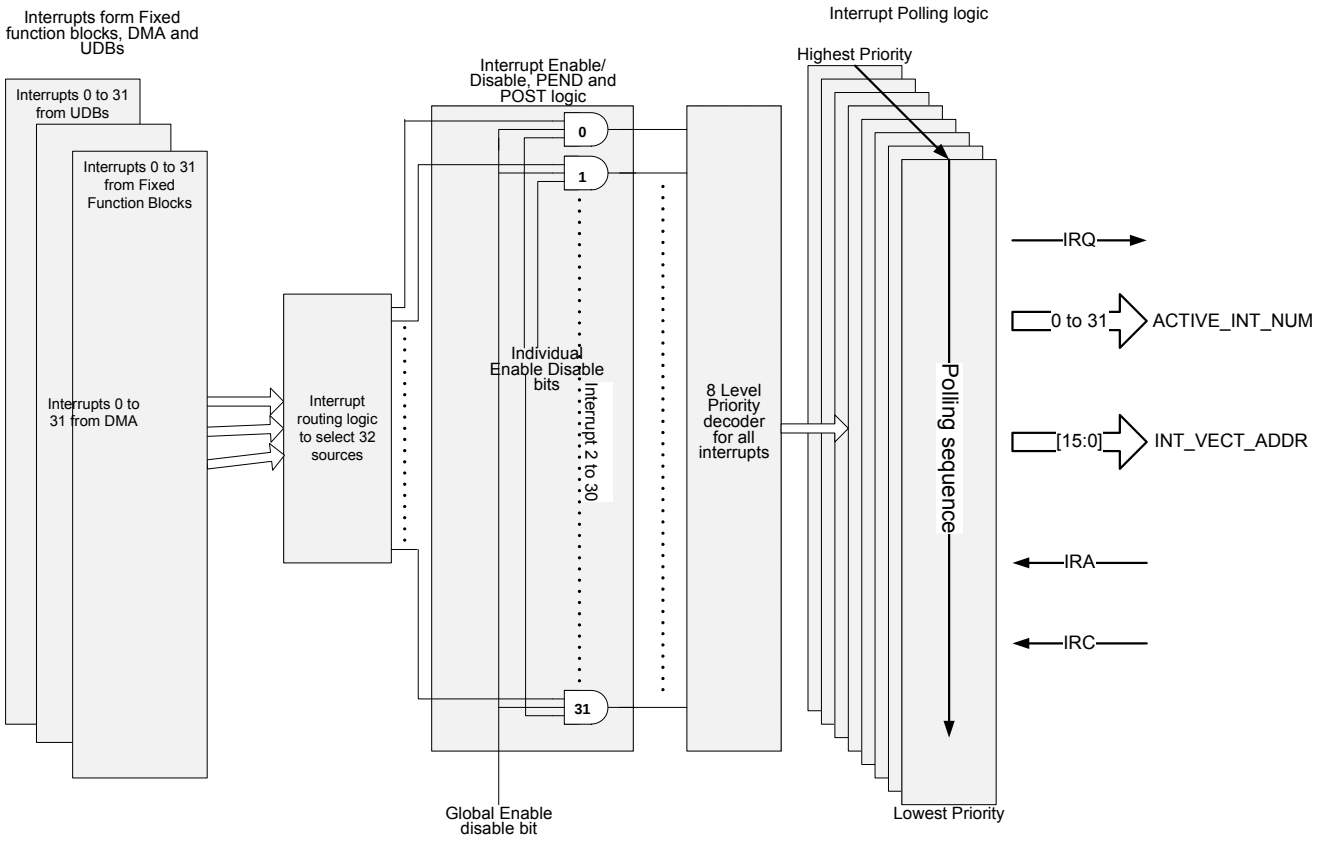
The total interrupt latency (ISR execution)

= POST + PEND + IRQ + IRA + Completing current instruction and branching

= 1+1+1+2+7 cycles

= 12 cycles

Figure 4-3. Interrupt Structure



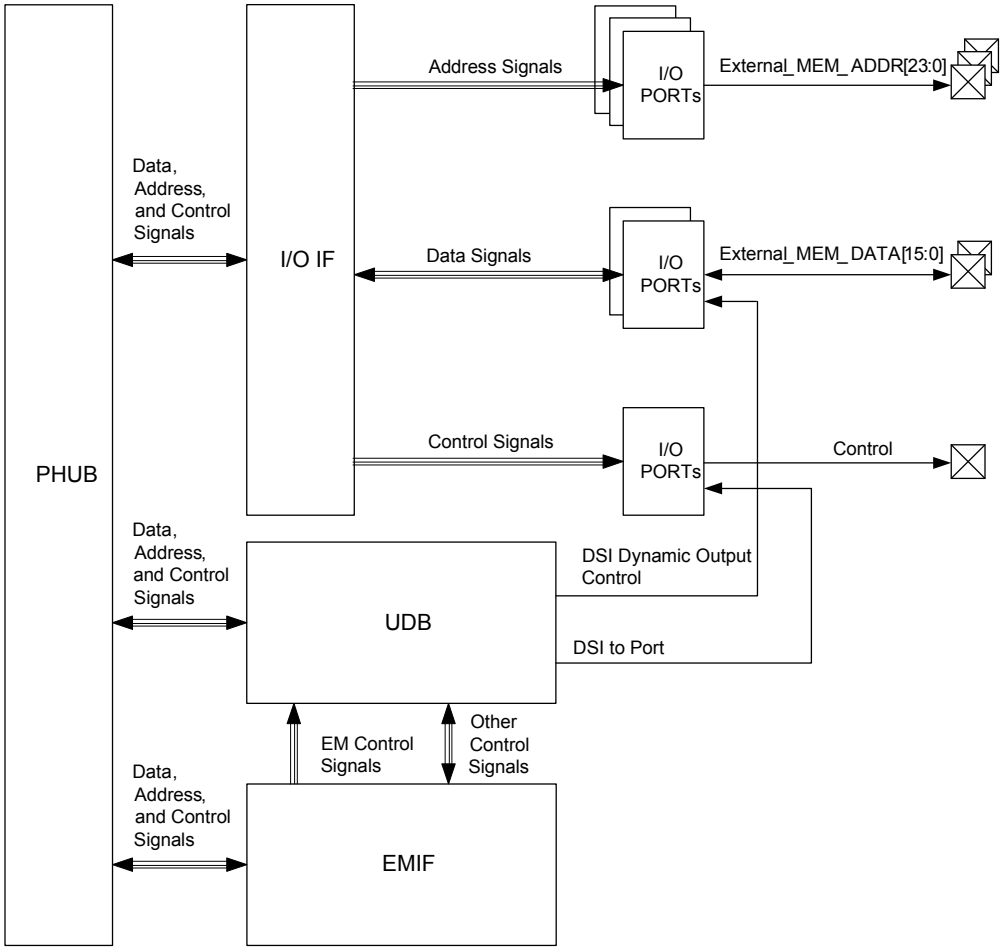
5.6 External Memory Interface

CY8C34 provides an External Memory Interface (EMIF) for connecting to external memory devices. The connection allows read and write accesses to external memories. The EMIF operates in conjunction with UDBs, I/O ports, and other hardware to generate external memory address and control signals. At 33 MHz, each memory access cycle takes four bus clock cycles.

Figure 5-1 is the EMIF block diagram. The EMIF supports synchronous and asynchronous memories. The CY8C34 supports only one type of external memory device at a time.

External memory can be accessed via the 8051 xdata space; up to 24 address bits can be used. See "xdata Space" section on page 26. The memory can be 8 or 16 bits wide.

Figure 5-1. EMIF Block Diagram



5.7 Memory Map

The CY8C34 8051 memory map is very similar to the MCS-51 memory map.

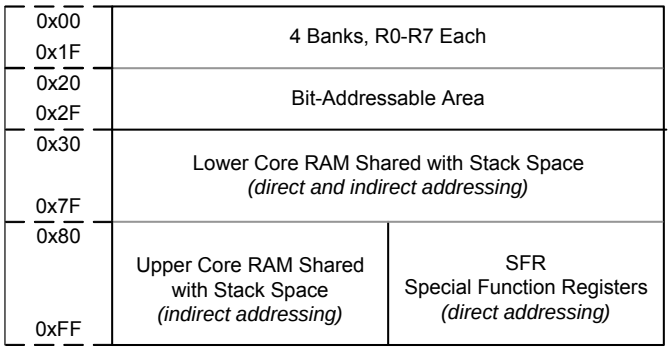
5.7.1 Code Space

The CY8C34 8051 code space is 64 KB. Only main flash exists in this space. See the "Flash Program Memory" section on page 22.

5.7.2 Internal Data Space

The CY8C34 8051 internal data space is 384 bytes, compressed within a 256-byte space. This space consists of 256 bytes of RAM (in addition to the SRAM mentioned in Static RAM on page 22) and a 128-byte space for Special Function Registers (SFRs). See Figure 5-2. The lowest 32 bytes are used for 4 banks of registers R0-R7. The next 16 bytes are bit-addressable.

Figure 5-2. 8051 Internal Data Space



In addition to the register or bit address modes used with the lower 48 bytes, the lower 128 bytes can be accessed with direct or indirect addressing. With direct addressing mode, the upper 128 bytes map to the SFRs. With indirect addressing mode, the upper 128 bytes map to RAM. Stack operations use indirect addressing; the 8051 stack space is 256 bytes. See the "Addressing Modes" section on page 12

5.7.3 SFRs

The Special Function Register (SFR) space provides access to frequently accessed registers. The memory map for the SFR memory space is shown in Table 5-4.

Table 5-4. SFR Map

Address	0/8	1/9	2/A	3/B	4/C	5/D	6/E	7/F
0×F8	SFRPRT15DR	SFRPRT15PS	SFRPRT15SEL					
0×F0	B		SFRPRT12SEL					
0×E8	SFRPRT12DR	SFRPRT12PS	MXAX					
0×E0	ACC							
0×D8	SFRPRT6DR	SFRPRT6PS	SFRPRT6SEL					
0×D0	PSW							
0×C8	SFRPRT5DR	SFRPRT5PS	SFRPRT5SEL					
0×C0	SFRPRT4DR	SFRPRT4PS	SFRPRT4SEL					
0×B8								
0×B0	SFRPRT3DR	SFRPRT3PS	SFRPRT3SEL					
0×A8	IE							
0×A0	P2AX		SFRPRT1SEL					
0×98	SFRPRT2DR	SFRPRT2PS	SFRPRT2SEL					
0×90	SFRPRT1DR	SFRPRT1PS		DPX0		DPX1		
0×88		SFRPRT0PS	SFRPRT0SEL					
0×80	SFRPRT0DR	SP	DPL0	DPH0	DPL1	DPH1	DPS	

The CY8C34 family provides the standard set of registers found on industry standard 8051 devices. In addition, the CY8C34 devices add SFRs to provide direct access to the I/O ports on the device. The following sections describe the SFRs added to the CY8C34 family.

5.7.4 XData Space Access SFRs

The 8051 core features dual DPTR registers for faster data transfer operations. The data pointer select SFR, DPS, selects which data pointer register, DPTR0 or DPTR1, is used for the following instructions:

- MOVX @DPTR, A
- MOVX A, @DPTR
- MOVC A, @A+DPTR
- JMP @A+DPTR
- INC DPTR
- MOV DPTR, #data16

The extended data pointer SFRs, DPX0, DPX1, MXAX, and P2AX, hold the most significant parts of memory addresses during access to the xdata space. These SFRs are used only with the MOVX instructions.

During a MOVX instruction using the DPTR0/DPTR1 register, the most significant byte of the address is always equal to the contents of DPX0/DPX1. During a MOVX instruction using the R0 or R1 register, the most significant byte of the address is always equal to the contents of MXAX, and the next most significant byte is always equal to the contents of P2AX.

5.7.5 I/O Port SFRs

The I/O ports provide digital input sensing, output drive, pin interrupts, connectivity for analog inputs and outputs, LCD, and access to peripherals through the DSI. Full information on I/O ports is found in I/O System and Routing on page 36.

I/O ports are linked to the CPU through the PHUB and are also available in the SFRs. Using the SFRs allows faster access to a limited set of I/O port registers, while using the PHUB allows boot configuration and access to all I/O port registers.

Each SFR supported I/O port provides three SFRs:

- SFRPRTxDR sets the output data state of the port (where x is port number and includes ports 0-6, 12 and 15)
- The SFRPRTxSEL selects whether the PHUB PRTxDR register or the SFRPRTxDR controls each pin's output buffer within the port. If a SFRPRTxSEL[y] bit is high, the corresponding SFRPRTxDR[y] bit sets the output state for that pin. If a SFRPRTxSEL[y] bit is low, the corresponding PRTxDR[y] bit sets the output state of the pin (where y varies from 0 to 7).
- The SFRPRTxPS is a read only register that contains pin state values of the port pins.

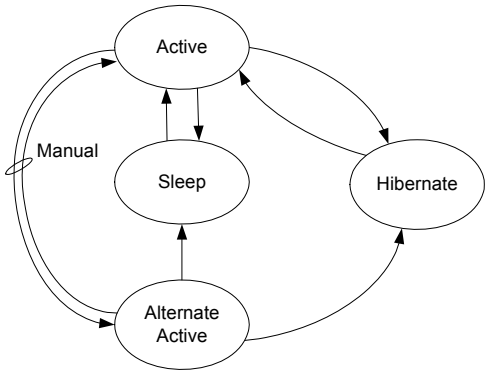
5.7.5.1 xdata Space

The 8051 xdata space is 24-bit, or 16 MB in size. The majority of this space is not "external"—it is used by on-chip components. See Table 5-5. External, that is, off-chip, memory can be accessed using the EMIF. See External Memory Interface on page 24.

Table 5-5. XDATA Data Address Map

Address Range	Purpose
0×00 0000 – 0×00 1FFF	SRAM
0×00 4000 – 0×00 42FF	Clocking, PLLs, and oscillators
0×00 4300 – 0×00 43FF	Power management
0×00 4400 – 0×00 44FF	Interrupt controller
0×00 4500 – 0×00 45FF	Ports interrupt control
0×00 4700 – 0×00 47FF	Flash programming interface
0×00 4800 - 0×00 48FF	Cache controller
0×00 4900 – 0×00 49FF	I^2C controller
0×00 4E00 – 0×00 4EFF	Decimator
0×00 4F00 – 0×00 4FFF	Fixed timer/counter/PWMs
0×00 5000 – 0×00 51FF	I/O ports control
0×00 5400 – 0×00 54FF	External Memory Interface (EMIF) control registers
0×00 5800 – 0×00 5FFF	Analog Subsystem interface
0×00 6000 – 0×00 60FF	USB controller
0×00 6400 – 0×00 6FFF	UDB Working Registers
0×00 7000 – 0×00 7FFF	PHUB configuration
0×00 8000 – 0×00 8FFF	EEPROM
0×00 A000 – 0×00 A400	CAN
0×01 0000 – 0×01 FFFF	Digital Interconnect configuration
0×05 0220 – 0×05 02F0	Debug controller
0×08 0000 – 0×08 1FFF	Flash ECC bytes
0×80 0000 – 0×FF FFFF	External Memory Interface

Figure 6-5. Power Mode Transitions



6.2.1.1 Active Mode

Active mode is the primary operating mode of the device. When in active mode, the active configuration template bits control which available resources are enabled or disabled. When a resource is disabled, the digital clocks are gated, analog bias currents are disabled, and leakage currents are reduced as appropriate. User firmware can dynamically control subsystem power by setting and clearing bits in the active configuration template. The CPU can disable itself, in which case the CPU is automatically reenabled at the next wakeup event.

When a wakeup event occurs, the global mode is always returned to active, and the CPU is automatically enabled, regardless of its template settings. Active mode is the default global power mode upon boot.

6.2.1.2 Alternate Active Mode

Alternate Active mode is very similar to Active mode. In alternate active mode, fewer subsystems are enabled, to reduce power consumption. One possible configuration is to turn off the CPU and flash, and run peripherals at full speed.

6.2.1.3 Sleep Mode

Sleep mode reduces power consumption when a resume time of 15 µs is acceptable. The wake time is used to ensure that the regulator outputs are stable enough to directly enter active mode.

6.2.1.4 Hibernate Mode

In hibernate mode nearly all of the internal functions are disabled. Internal voltages are reduced to the minimal level to keep vital systems alive. Configuration state is preserved in hibernate mode and SRAM memory is retained. GPIOs configured as digital outputs maintain their previous values and external GPIO pin interrupt settings are preserved. The device can only return from hibernate mode in response to an external I/O interrupt. The resume time from hibernate mode is less than 100 µs.

To achieve an extremely low current, the hibernate regulator has limited capacity. This limits the frequency of any signal present on the input pins - no GPIO should toggle at a rate greater than 10 kHz while in hibernate mode. If pins must be toggled at a high rate while in a low power mode, use sleep mode instead.

6.2.1.5 Wakeup Events

Wakeup events are configurable and can come from an interrupt or device reset. A wakeup event restores the system to active mode. Firmware enabled interrupt sources include internally generated interrupts, power supervisor, central timewheel, and I/O interrupts. Internal interrupt sources can come from a variety of peripherals, such as analog comparators and UDBs. The central timewheel provides periodic interrupts to allow the system to wake up, poll peripherals, or perform real-time functions. Reset event sources include the external reset I/O pin (XRES), WDT, and Precision Reset (PRES).

6.2.2 Boost Converter

Applications that use a supply voltage of less than 1.71 V, such as solar panels or single cell battery supplies, may use the on-chip boost converter to generate a minimum of 1.8 V supply voltage. The boost converter may also be used in any system that requires a higher operating voltage than the supply provides such as driving 5.0 V LCD glass in a 3.3 V system. With the addition of an inductor, Schottky diode, and capacitors, it produces a selectable output voltage sourcing enough current to operate the PSoC and other on-board components.

The boost converter accepts an input voltage V_{BAT} from 0.5 V to 3.6 V, and can start up with V_{BAT} as low as 0.5 V. The converter provides a user configurable output voltage of 1.8 to 5.0 V (V_{OUT}) in 100 mV increments. V_{BAT} is typically less than V_{OUT}; if V_{BAT} is greater than or equal to V_{OUT}, then V_{OUT} will be slightly less than V_{BAT} due to resistive losses in the boost converter. The block can deliver up to 50 mA (I_{BOOST}) depending on configuration to both the PSoC device and external components. The sum of all current sinks in the design including the PSoC device, PSoC I/O pin loads, and external component loads must be less than the I_{BOOST} specified maximum current.

Four pins are associated with the boost converter: VBAT, VSSB, VBOOST, and IND. The boosted output voltage is sensed at the VBOOST pin and must be connected directly to the chip's supply inputs; VDDA, VDDD, and VDDIO if used to power the PSoC device.

The boost converter requires four components in addition to those required in a non-boost design, as shown in Figure 6-6 on page 33. A 22 µF capacitor (CBAT) is required close to the VBAT pin to provide local bulk storage of the battery voltage and provide regulator stability. A diode between the battery and VBAT pin should not be used for reverse polarity protection because the diodes forward voltage drop reduces the V_{BAT} voltage. Between the VBAT and IND pins, an inductor of 4.7 µH, 10 µH, or 22 µH is required. The inductor value can be optimized to increase the boost converter efficiency based on input voltage, output voltage, temperature, and current. Inductor size is determined by following the design guidance in this chapter and electrical specifications. The inductor must be placed within 1 cm of the VBAT and IND pins and have a minimum saturation current of 750 mA. Between the IND and VBOOST pins, place a Schottky diode within 1 cm of the pins. The Schottky diode shall have a forward current rating of at least 1.0 A and a reverse voltage of at least 20 V. Connect a 22-µF bulk capacitor (CBOOST) close to VBOOST to provide regulator output stability. It is important to sum the total capacitance connected to the VBOOST pin and ensure the maximum C_{BOOST} specification is not exceeded. All capacitors must be rated for a minimum of 10 V to minimize capacitive losses due to voltage de-rating.

boost typically draws 250 µA in active mode and 25 µA in standby mode. The boost operating modes must be used in conjunction with chip power modes to minimize total power consumption. Table 6-4 lists the boost power modes available in different chip power modes.

Table 6-4. Chip and Boost Power Modes Compatibility

Chip Power Modes	Boost Power Modes
Chip-active or alternate active mode	Boost must be operated in its active mode.
Chip-sleep mode	Boost can be operated in either active or standby mode. In boost standby mode, the chip must wake up periodically for boost active-mode refresh.
Chip-hibernate mode	Boost can be operated in its active mode. However, it is recommended not to use the boost in chip hibernate mode due to the higher current consumption in boost active mode.

6.2.2.1 Boost Firmware Requirements

To ensure boost inrush current is within specification at startup, the **Enable Fast IMO During Startup** value must be unchecked in the PSoC Creator IDE. The **Enable Fast IMO During Startup** option is found in PSoC Creator in the design wide resources (cydwr) file **System** tab. Un-checking this option configures the device to run at 12 MHz vs 48 MHz during startup while configuring the device. The slower clock speed results in reduced current draw through the boost circuit.

6.2.2.2 Boost Design Process

Correct operation of the boost converter requires specific component values determined for each designs unique operating conditions. The C_{BAT} capacitor, Inductor, Schottky diode, and C_{BOOST} capacitor components are required with the values specified in the electrical specifications, Table 11-7 on page 77. The only variable component value is the inductor L_{BOOST} which is primarily sized for correct operation of the boost across operating conditions and secondarily for efficiency. Additional operating region constraints exist for V_{OUT}, V_{BAT}, I_{OUT}, and T_A.

The following steps must be followed to determine boost converter operating parameters and L_{BOOST} value.

1. Choose desired V_{BAT}, V_{OUT}, T_A, and I_{OUT} operating condition ranges for the application.
2. Determine if V_{BAT} and V_{OUT} ranges fit the boost operating range based on the **T_A range over V_{BAT} and V_{OUT}** chart, Figure 11-8 on page 77. If the operating ranges are not met, modify the operating conditions or use an external boost regulator.
3. Determine if the desired ambient temperature (T_A) range fits the ambient temperature operating range based on the **T_A range over V_{BAT} and V_{OUT}** chart, Figure 11-8 on page 77. If the temperature range is not met, modify the operating conditions and return to step 2, or use an external boost regulator.
4. Determine if the desired output current (I_{OUT}) range fits the output current operating range based on the **I_{OUT} range over V_{BAT} and V_{OUT}** chart, Figure 11-9 on page 77. If the output current range is not met, modify the operating conditions and return to step 2, or use an external boost regulator.
5. Find the allowed inductor values based on the **L_{BOOST} values over V_{BAT} and V_{OUT}** chart, Figure 11-10 on page 77.
6. Based on the allowed inductor values, inductor dimensions, inductor cost, boost efficiency, and V_{RIPPLE} choose the optimum inductor value for the system. Boost efficiency and V_{RIPPLE} typical values are provided in the **Efficiency vs V_{BAT}** and **V_{RIPPLE} vs V_{BAT}** charts, Figure 11-11 on page 78 through Figure 11-14 on page 78. In general, if high efficiency and low V_{RIPPLE} are most important, then the highest allowed inductor value should be used. If low inductor cost or small inductor size are most important, then one of the smaller allowed inductor values should be used. If the allowed inductor(s) efficiency, V_{RIPPLE}, cost or dimensions are not acceptable for the application than an external boost regulator should be used.

6.3 Reset

CY8C34 has multiple internal and external reset sources available. The reset sources are:

- Power source monitoring – The analog and digital power voltages, VDDA, VDDD, VCCA, and VCCD are monitored in several different modes during power up, active mode, and sleep mode (buzzing). If any of the voltages goes outside predetermined ranges then a reset is generated. The monitors are programmable to generate an interrupt to the processor under certain conditions before reaching the reset thresholds.
- External – The device can be reset from an external source by pulling the reset pin ($\overline{\text{XRES}}$) low. The $\overline{\text{XRES}}$ pin includes an internal pull-up to VDDIO1. VDDD, VDDA, and VDDIO1 must all have voltage applied before the part comes out of reset.
- Watchdog timer – A watchdog timer monitors the execution of instructions by the processor. If the watchdog timer is not reset by firmware within a certain period of time, the watchdog timer generates a reset.
- Software – The device can be reset under program control.

For most designs, the default values in Table 7-2 will provide excellent performance without any calculations. The default values were chosen to use standard resistor values between the minimum and maximum limits. The values in Table 7-2 work for designs with 1.8 V to 5.0V V_{DD}, less than 200-pF bus capacitance (C_B), up to 25 µA of total input leakage (I_{IL}), up to 0.4 V output voltage level (V_{OL}), and a max V_{IH} of 0.7 * V_{DD}. Standard Mode and Fast Mode can use either GPIO or SIO PSoC pins. Fast Mode Plus requires use of SIO pins to meet the V_{OL} spec at 20 mA. Calculation of custom pull-up resistor values is required; if your design does not meet the default assumptions, you use series resistors (RS) to limit injected noise, or you need to maximize the resistor value for low power consumption.

Table 7-2. Recommended default Pull-up Resistor Values

	R_P	Units
Standard Mode – 100 kbps	4.7 k, 5%	Ω
Fast Mode – 400 kbps	1.74 k, 1%	Ω
Fast Mode Plus – 1 Mbps	620, 5%	Ω

Calculation of the ideal pull-up resistor value involves finding a value between the limits set by three equations detailed in the NXP I^2C specification. These equations are:

Equation 1:

$$R_{PMIN} = (V_{DD}(max) - V_{OL}(max))/(I_{OL}(min))$$

Equation 2:

$$R_{PMAX} = T_R(max)/0.8473 \times C_B(max)$$

Equation 3:

$$R_{PMAX} = V_{DD}(min) - V_{IH}(min) + V_{NH}(min)/I_{IH}(max)$$

Equation parameters:

V_{DD} = Nominal supply voltage for I^2C bus

V_{OL} = Maximum output low voltage of bus devices.

I_{OL}= Low-level output current from I^2C specification

T_R = Rise Time of bus from I^2C specification

C_B = Capacitance of each bus line including pins and PCB traces

V_{IH} = Minimum high-level input voltage of all bus devices

V_{NH} = Minimum high-level input noise margin from I^2C specification

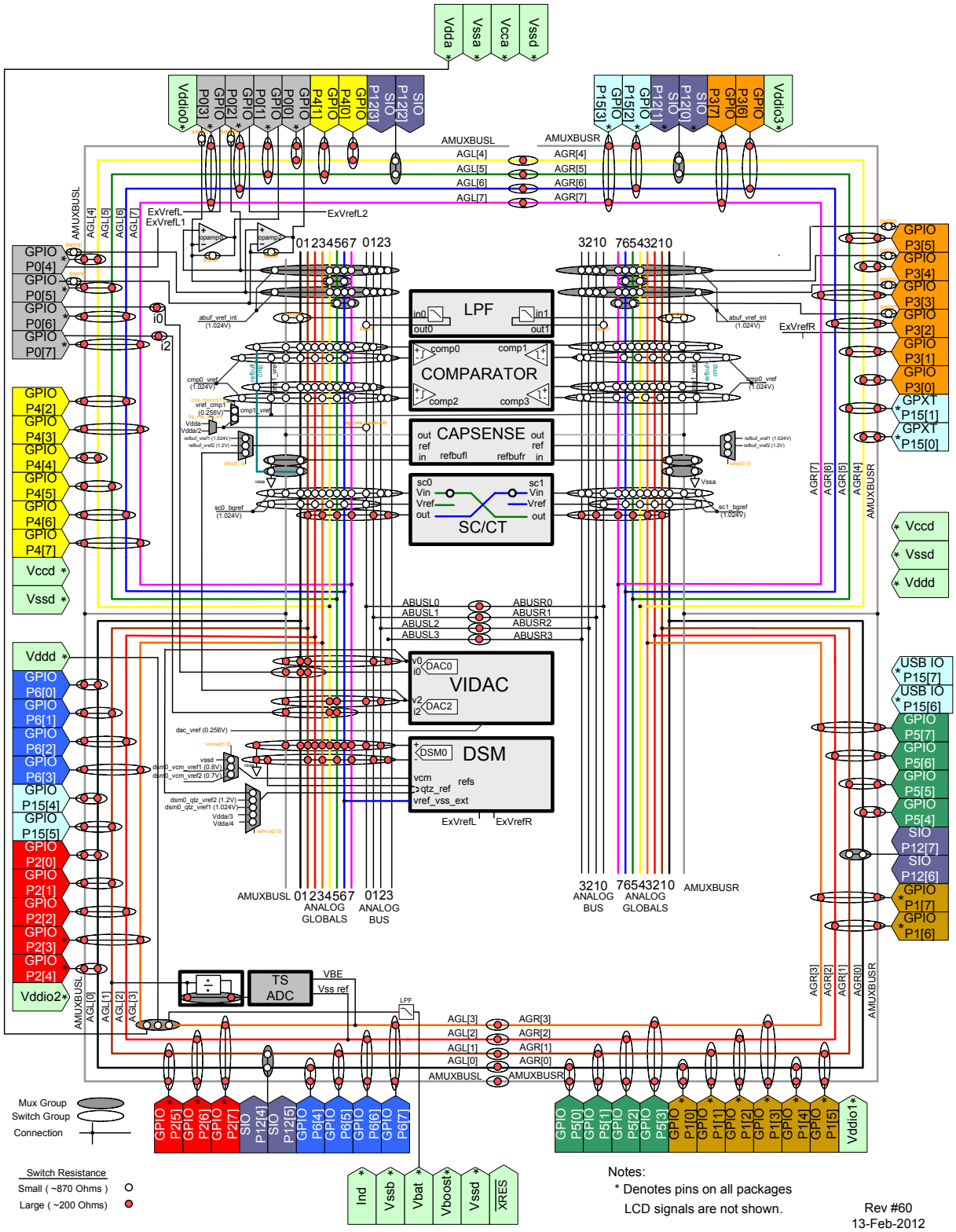
I_{IH} = Total input leakage current of all devices on the bus

The supply voltage (V_{DD}) limits the minimum pull-up resistor value due to bus devices maximum low output voltage (V_{OL}) specifications. Lower pull-up resistance increases current through the pins and can, therefore, exceed the spec conditions of V_{OL}. Equation 1 is derived using Ohm's law to determine the minimum resistance that will still meet the V_{OL} specification at 3 mA for standard and fast modes, and 20 mA for fast mode plus at the given V_{DD}.

Equation 2 determines the maximum pull-up resistance due to bus capacitance. Total bus capacitance is comprised of all pin, wire, and trace capacitance on the bus. The higher the bus capacitance, the lower the pull-up resistance required to meet the specified bus speeds rise time due to RC delays. Choosing a pull-up resistance higher than allowed can result in failing timing requirements resulting in communication errors. Most designs with five or less I^2C devices and up to 20 centimeters of bus trace length have less than 100 pF of bus capacitance.

A secondary effect that limits the maximum pull-up resistor value is total bus leakage calculated in Equation 3. The primary source of leakage is I/O pins connected to the bus. If leakage is too high, the pull-ups will have difficulty maintaining an acceptable V_{IH} level causing communication errors. Most designs with five or less I^2C devices on the bus have less than 10 µA of total leakage current.

Figure 8-2. CY8C34 Analog Interconnect



To preserve detail of this figure, this figure is best viewed with a PDF display program or printed on a 11" × 17" paper.

8.2.3 Start of Conversion Input

The SoC signal is used to start an ADC conversion. A digital clock or UDB output can be used to drive this input. It can be used when the sampling period must be longer than the ADC conversion time or when the ADC must be synchronized to other hardware. This signal is optional and does not need to be connected if ADC is running in a continuous mode.

8.2.4 End of Conversion Output

The EoC signal goes high at the end of each ADC conversion. This signal may be used to trigger either an interrupt or DMA request.

8.3 Comparators

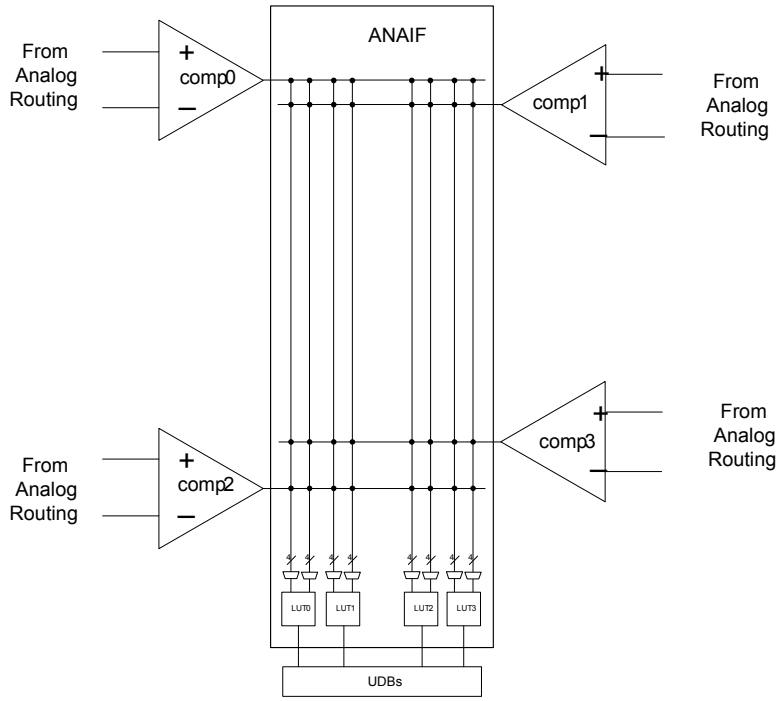
The CY8C34 family of devices contains four comparators in a device. Comparators have these features:

- Input offset factory trimmed to less than 5 mV
- Rail-to-rail common mode input range (V_{SSA} to VDDA)
- Speed and power can be traded off by using one of three modes: fast, slow, or ultra low-power
- Comparator outputs can be routed to lookup tables to perform simple logic functions and then can also be routed to digital blocks
- The positive input of the comparators may be optionally passed through a low pass filter. Two filters are provided
- Comparator inputs can be connections to GPIO, DAC outputs and SC block outputs

8.3.1 Input and Output Interface

The positive and negative inputs to the comparators come from the analog global buses, the analog mux line, the analog local bus and precision reference through multiplexers. The output from each comparator could be routed to any of the two input LUTs. The output of that LUT is routed to the UDB Digital System Interface.

Figure 8-5. Analog Comparator



11. Electrical Specifications

Specifications are valid for –40 °C ≤ T_A ≤ 85 °C and T_J ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted. The unique flexibility of the PSoC UDBs and analog blocks enable many functions to be implemented in PSoC Creator components, see the component data sheets for full AC/DC specifications of individual functions. See the "Example Peripherals" section on page 43 for further explanation of PSoC Creator components.

11.1 Absolute Maximum Ratings

Table 11-1. Absolute Maximum Ratings DC Specifications[18]

Parameter	Description	Conditions	Min	Typ	Max	Units
V_{DDA}	Analog supply voltage relative to V_{SSA}		–0.5	–	6	V
V_{DDD}	Digital supply voltage relative to V_{SSD}		–0.5	–	6	V
V_{DDIO}	I/O supply voltage relative to V_{SSD}		–0.5	–	6	V
V_{CCA}	Direct analog core voltage input		–0.5	–	1.95	V
V_{CCD}	Direct digital core voltage input		–0.5	–	1.95	V
V_{SSA}	Analog ground voltage		V_{SSD} –0.5	–	V_{SSD} + 0.5	V
V_{GPIO}[19]	DC input voltage on GPIO	Includes signals sourced by V_{DDA} and routed internal to the pin	V_{SSD} –0.5	–	V_{DDIO} + 0.5	V
V_{SIO}	DC input voltage on SIO	Output disabled	V_{SSD} –0.5	–	7	V
		Output enabled	V_{SSD} –0.5	–	6	V
V_{IND}	Voltage at boost converter input		0.5	–	5.5	V
V_{BAT}	Boost converter supply		V_{SSD} –0.5	–	5.5	V
I_{VDDIO}	Current per V_{DDIO} supply pin		–	–	100	mA
I_{GPIO}	GPIO current		–30	–	41	mA
I_{SIO}	SIO current		–49	–	28	mA
I_{USBIO}	USBIO current		–56	–	59	mA
V_{EXTREF}	ADC external reference inputs	Pins P0[3], P3[2]	–	–	2	V
LU	Latch up current[20]		–140	–	140	mA
ESD_{HBM}	Electrostatic discharge voltage, Human body model	V_{SSA} tied to V_{SSD}	2200	–	–	V
		V_{SSA} not tied to V_{SSD}	750	–	–	V
ESD_{CDM}	Electrostatic discharge voltage, Charge device model		500	–	–	V

Notes

18. Usage above the absolute maximum conditions listed in Table 11-1 may cause permanent damage to the device. Exposure to Absolute Maximum conditions for extended periods of time may affect device reliability. The Maximum Storage Temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below Absolute Maximum conditions but above normal operating conditions, the device may not operate to specification.
19. The V_{DDIO} supply voltage must be greater than the maximum voltage on the associated GPIO pins. Maximum voltage on GPIO pin ≤ V_{DDIO} ≤ V_{DDA}.
20. Meets or exceeds JEDEC Spec EIA/JESD78 IC Latch-up Test.

Figure 11-17. SIO Output High Voltage and Current, Unregulated Mode

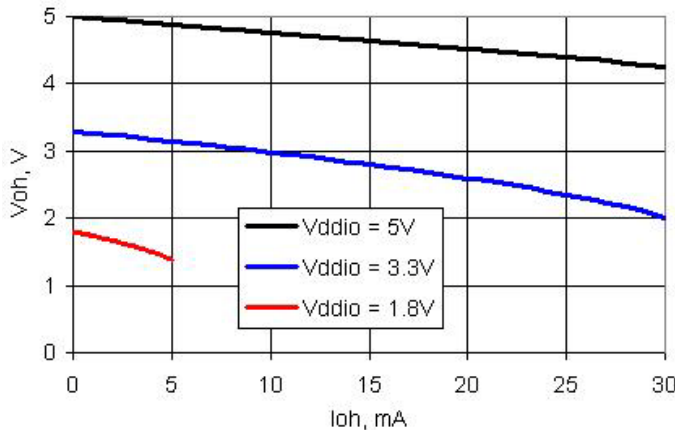


Figure 11-18. SIO Output Low Voltage and Current, Unregulated Mode

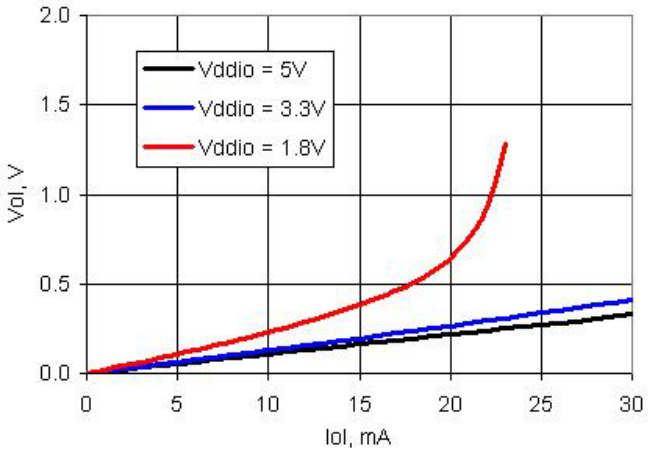


Figure 11-19. SIO Output High Voltage and Current, Regulated Mode

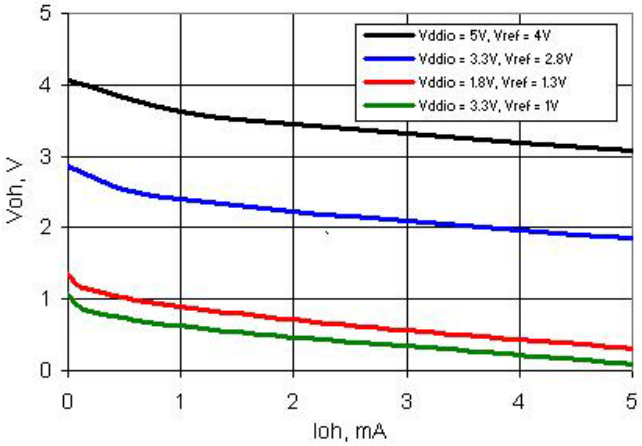


Table 11-12. SIO AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
TriseF	Rise time in Fast Strong Mode (90/10%)[44]	Cload = 25 pF, V_{DDIO} = 3.3 V	–	–	12	ns
TfallF	Fall time in Fast Strong Mode (90/10%)[44]	Cload = 25 pF, V_{DDIO} = 3.3 V	–	–	12	ns
TriseS	Rise time in Slow Strong Mode (90/10%)[44]	Cload = 25 pF, V_{DDIO} = 3.0 V	–	–	75	ns
TfallS	Fall time in Slow Strong Mode (90/10%)[44]	Cload = 25 pF, V_{DDIO} = 3.0 V	–	–	60	ns

Note
44. Based on device characterization (Not production tested).

Table 11-12. SIO AC Specifications *(continued)*

Parameter	Description	Conditions	Min	Typ	Max	Units
Fsioout	SIO output operating frequency					
	2.7 V < V_{DDIO} < 5.5 V, Unregulated output (GPIO) mode, fast strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	33	MHz
	1.71 V < V_{DDIO} < 2.7 V, Unregulated output (GPIO) mode, fast strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	16	MHz
	3.3 V < V_{DDIO} < 5.5 V, Unregulated output (GPIO) mode, slow strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	5	MHz
	1.71 V < V_{DDIO} < 3.3 V, Unregulated output (GPIO) mode, slow strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	4	MHz
	2.7 V < V_{DDIO} < 5.5 V, Regulated output mode, fast strong drive mode	Output continuously switching into 25 pF	–	–	20	MHz
	1.71 V < V_{DDIO} < 2.7 V, Regulated output mode, fast strong drive mode	Output continuously switching into 25 pF	–	–	10	MHz
	1.71 V < V_{DDIO} < 5.5 V, Regulated output mode, slow strong drive mode	Output continuously switching into 25 pF	–	–	2.5	MHz
Fsioin	SIO input operating frequency					
	1.71 V ≤ V_{DDIO} ≤ 5.5 V	90/10% V_{DDIO}	–	–	33	MHz

Figure 11-20. SIO Output Rise and Fall Times, Fast Strong Mode, V_{DDIO} = 3.3 V, 25 pF Load

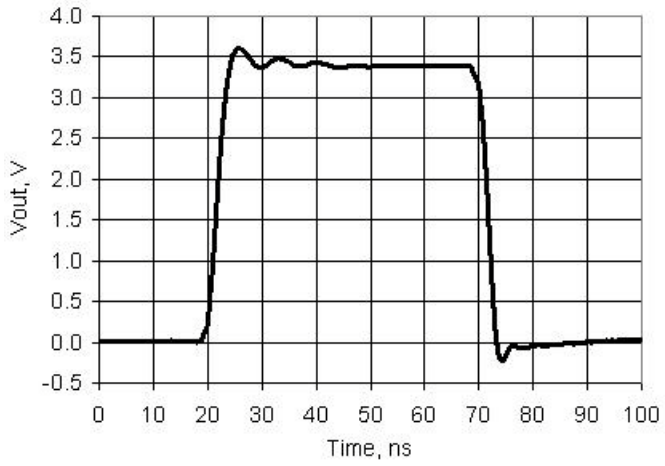


Figure 11-21. SIO Output Rise and Fall Times, Slow Strong Mode, V_{DDIO} = 3.3 V, 25 pF Load

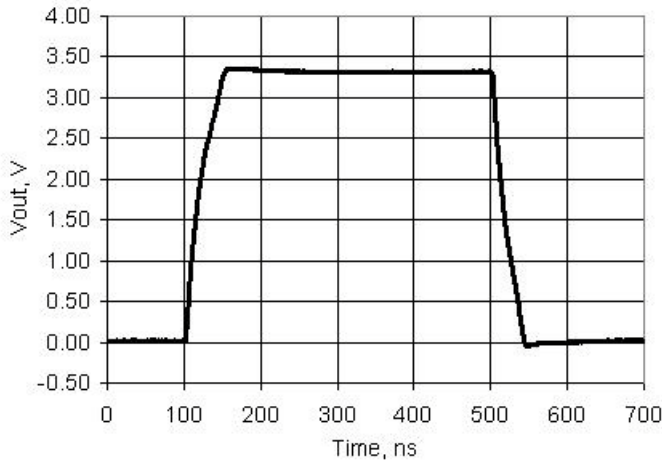


Figure 11-22. USBIO Output High Voltage and Current, GPIO Mode

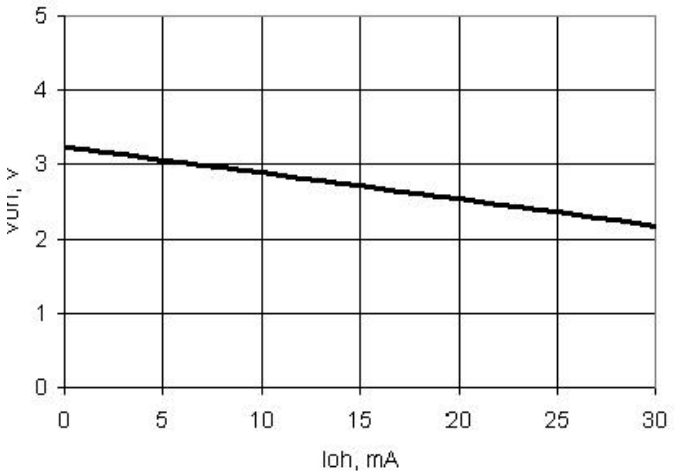


Figure 11-23. USBIO Output Low Voltage and Current, GPIO Mode

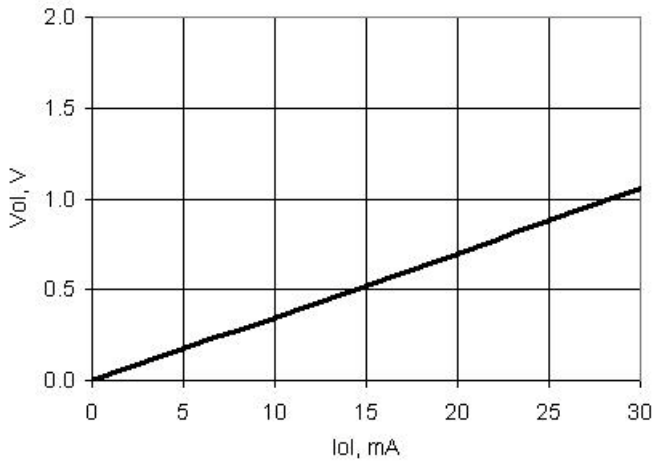


Table 11-15. USBIO AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
Tdrate	Full-speed data rate average bit rate		12 – 0.25%	12	12 + 0.25%	MHz
Tjr1	Receiver data jitter tolerance to next transition		–8	–	8	ns
Tjr2	Receiver data jitter tolerance to pair transition		–5	–	5	ns
Tdj1	Driver differential jitter to next transition		–3.5	–	3.5	ns
Tdj2	Driver differential jitter to pair transition		–4	–	4	ns
Tfdeop	Source jitter for differential transition to SE0 transition		–2	–	5	ns
Tfeopt	Source SE0 interval of EOP		160	–	175	ns
Tfeopr	Receiver SE0 interval of EOP		82	–	–	ns
Tfst	Width of SE0 interval during differential transition		–	–	14	ns
Fgpio_out	GPIO mode output operating frequency	$3\ V \le V_{DDD} \le 5.5\ V$	–	–	20	MHz
		$V_{DDD} = 1.71\ V$	–	–	6	MHz
Tr_gpio	Rise time, GPIO mode, 10%/90% V_{DDD}	$V_{DDD} > 3\ V$, 25 pF load	–	–	12	ns
		$V_{DDD} = 1.71\ V$, 25 pF load	–	–	40	ns
Tf_gpio	Fall time, GPIO mode, 90%/10% V_{DDD}	$V_{DDD} > 3\ V$, 25 pF load	–	–	12	ns
		$V_{DDD} = 1.71\ V$, 25 pF load	–	–	40	ns

Table 11-31. VDAC AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
F_{DAC}	Update rate	1 V scale	–	–	1000	ksps
		4 V scale	–	–	250	ksps
TsettleP	Settling time to 0.1%, step 25% to 75%	1 V scale, Cload = 15 pF	–	0.45	1	µs
		4 V scale, Cload = 15 pF	–	0.8	3.2	µs
TsettleN	Settling time to 0.1%, step 75% to 25%	1 V scale, Cload = 15 pF	–	0.45	1	µs
		4 V scale, Cload = 15 pF	–	0.7	3	µs
	Voltage noise	Range = 1 V, High speed mode, V_{DDA} = 5 V, 10 kHz	–	750	–	nV/sqrtHz

Figure 11-56. VDAC Step Response, Codes 0x40 - 0xC0, 1 V Mode, High speed mode, V_{DDA} = 5 V

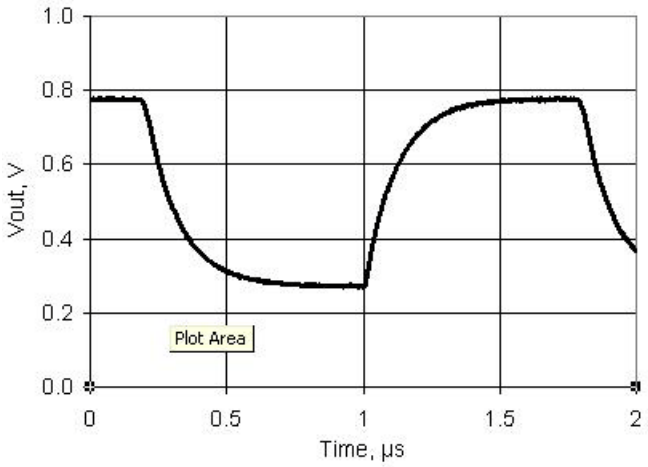


Figure 11-57. VDAC Glitch Response, Codes 0x7F - 0x80, 1 V Mode, High speed mode, V_{DDA} = 5 V

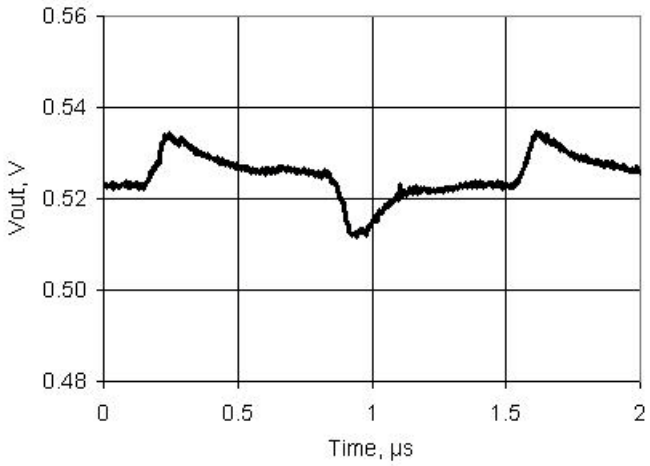


Figure 11-58. VDAC PSRR vs Frequency

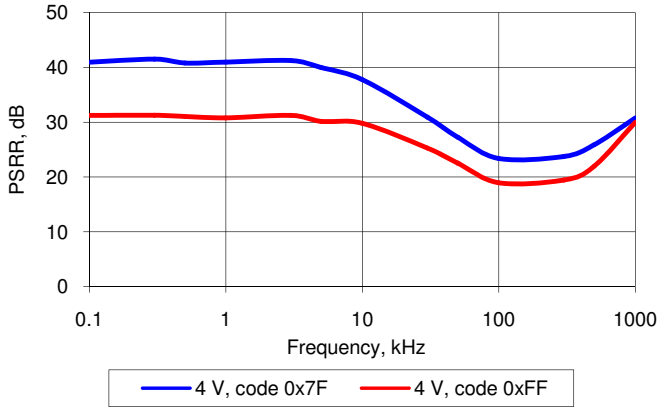
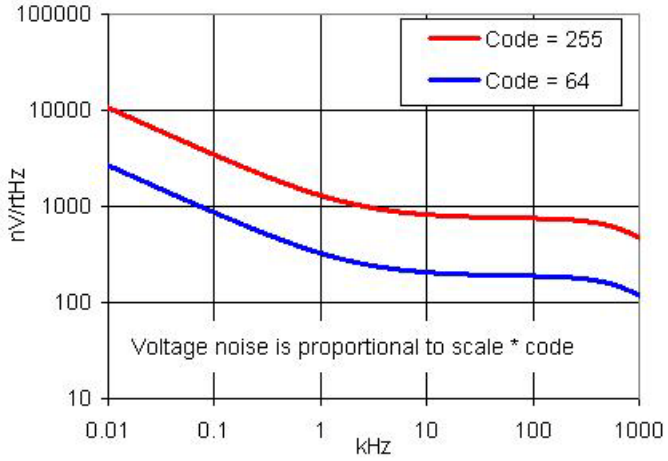


Figure 11-59. VDAC Voltage Noise, 1 V Mode, High speed mode, V_{DDA} = 5 V



11.8.5 SWD Interface

Figure 11-69. SWD Interface Timing

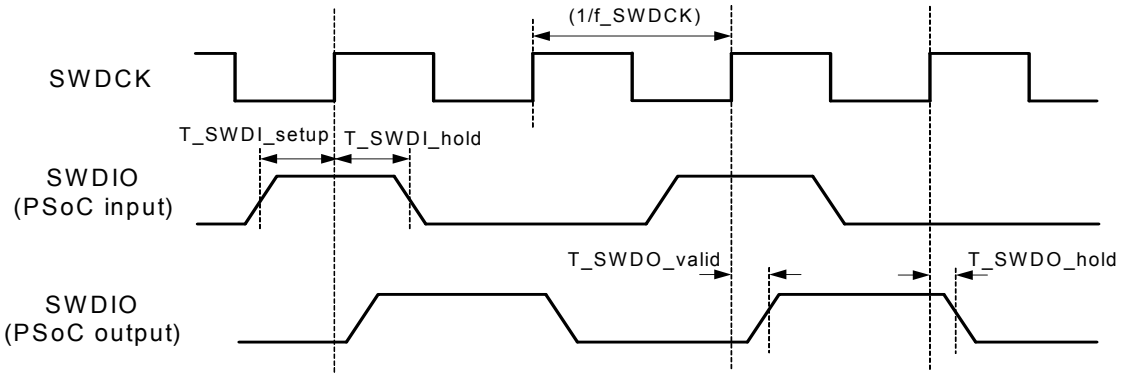


Table 11-71. SWD Interface AC Specifications[71]

Parameter	Description	Conditions	Min	Typ	Max	Units
f_SWDCK	SWDCLK frequency	3.3 V ≤ V_{DDD} ≤ 5 V	–	–	14[72]	MHz
		1.71 V ≤ V_{DDD} < 3.3 V	–	–	7[72]	MHz
		1.71 V ≤ V_{DDD} < 3.3 V, SWD over USBIO pins	–	–	5.5[72]	MHz
T_SWDI_setup	SWDIO input setup before SWDCK high	T = 1/f_SWDCK max	T/4	–	–	–
T_SWDI_hold	SWDIO input hold after SWDCK high	T = 1/f_SWDCK max	T/4	–	–	–
T_SWDO_valid	SWDCK high to SWDIO output	T = 1/f_SWDCK max	–	–	2T/5	–

11.8.6 SWV Interface

Table 11-72. SWV Interface AC Specifications[71]

Parameter	Description	Conditions	Min	Typ	Max	Units
	SWV mode SWV bit rate		–	–	33	Mbit

Notes
71. Based on device characterization (Not production tested).
72. ff_SWDCK must also be no more than 1/3 CPU clock frequency.

Figure 11-73. ILO Frequency Variation vs. Temperature

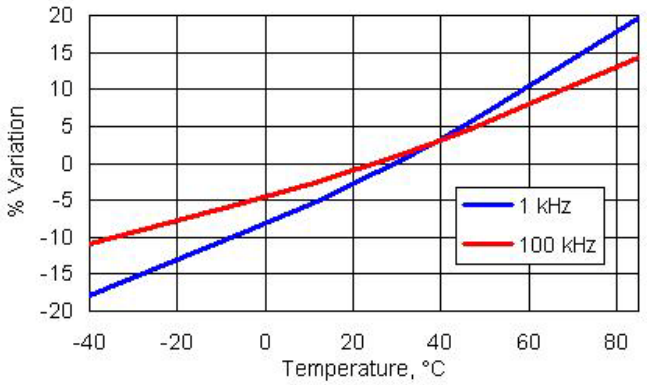
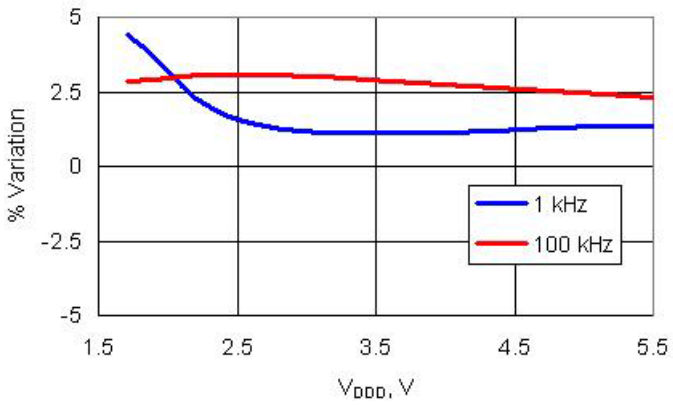


Figure 11-74. ILO Frequency Variation vs. V_{DD}



11.9.3 MHz External Crystal Oscillator

For more information on crystal or ceramic resonator selection for the MHzECO, refer to application note AN54439: PSoC 3 and PSoC 5 External Oscillators..

Table 11-77. MHzECO DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
I_{CC}	Operating current[75]	13.56 MHz crystal	–	3.8	–	mA

Table 11-78. MHzECO AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
F	Crystal frequency range		4	–	25	MHz

11.9.4 kHz External Crystal Oscillator

Table 11-79. kHzECO DC Specifications[75]

Parameter	Description	Conditions	Min	Typ	Max	Units
I_{CC}	Operating current	Low-power mode; CL = 6 pF	–	0.25	1.0	µA
DL	Drive level		–	–	1	µW

Table 11-80. kHzECO AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
F	Frequency		–	32.768	–	kHz
T_{ON}	Startup time	High-power mode	–	1	–	s

Note
75. Based on device characterization (Not production tested).